AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

1.-10. (Canceled)

11. (Currently Amended) A silicon carbide component of a semiconductor substrate processing apparatus, the silicon carbide component being porous and comprising an interior and an exposed surface, the silicon carbide component having been (i) made by a carbon conversion process that results in the silicon carbide component including free-carbon in the interior; (ii) treated to produce an exposed surface having free-carbon therein; and (iii) treated to remove the free-carbon such that at least the exposed surface is substantially free of the free-carbon, wherein the silicon carbide component is selected from the group consisting of a baffle plate, a plasma confinement ring and an edge ring.

12. (Currently Amended) The silicon carbide component of Claim 11, wherein the silicon carbide component is ~~selected from the group consisting of~~ a baffle plate~~, a plasma confinement ring, edge ring, focus ring, backing plate, chamber liner, electrode, wafer passage insert, window, plasma screen, and a chamber wall~~.

13. (Original) A semiconductor substrate processing apparatus comprising a plasma processing chamber and at least one silicon carbide component according to Claim 11 in the plasma processing chamber.

14. (Original) The semiconductor substrate processing apparatus of Claim 13, wherein the plasma processing chamber is an etching chamber.

15.-28. (Canceled)

29. (New) The silicon carbide component of Claim 11, wherein the silicon carbide component is a new component.

30. (New) The silicon carbide component of Claim 11, wherein the silicon carbide component has not been exposed to plasma in a semiconductor substrate processing apparatus.

31. (New) The silicon carbide component of Claim 11, wherein the silicon carbide component has not been exposed to plasma during the processing of production semiconductor substrates in a semiconductor substrate processing apparatus.

32. (New) The silicon carbide component of Claim 11, wherein the free-carbon comprises carbon clusters having a size of about 20 μm to about 200 μm.

33. (New) The silicon carbide component of Claim 11, wherein the exposed surface is a machined surface substantially free of the free-carbon and the interior of the silicon carbide component contains free-carbon.

34. (New) The silicon carbide component of Claim 11, wherein the silicon carbide component has a thickness of up to about ¼ inch.

35. (New) A silicon carbide component of a semiconductor substrate processing apparatus, the silicon carbide component comprising an interior and an exposed surface, the interior containing free-carbon and the exposed surface being substantially free of the free-carbon, wherein the silicon carbide component is selected from the group consisting of a baffle plate, a plasma confinement ring and an edge ring.

36. (New) The silicon carbide component of Claim 35, wherein the silicon carbide component is a baffle plate

37. (New) The silicon carbide component of Claim 35, wherein the silicon carbide component is a new component.

38. (New) The silicon carbide component of Claim 35, wherein the silicon carbide component has not been exposed to plasma in a semiconductor substrate processing apparatus.

39. (New) The silicon carbide component of Claim 35, wherein the silicon carbide component has not been exposed to plasma during the processing of production semiconductor substrates in a semiconductor substrate processing apparatus.

40. (New) The silicon carbide component of Claim 35, wherein the free-carbon comprises carbon clusters having a size of about 20 μm to about 200 μm.

41. (New) The silicon carbide component of Claim 35, wherein the exposed surface is a machined surface substantially free of the free-carbon and the interior of the silicon carbide component contains free-carbon.

42. (New) The silicon carbide component of Claim 35, wherein the silicon carbide component has a thickness of up to about ¼ inch.

43. (New) A silicon carbide baffle plate of a semiconductor substrate processing apparatus, the baffle plate comprising an interior and a machined exposed surface, the interior containing free-carbon particles or clusters and the exposed surface being substantially free of free-carbon.

44. (New) The silicon carbide baffle plate of Claim 43, wherein the baffle plate is a new component.